

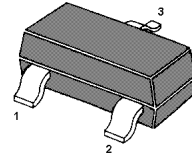
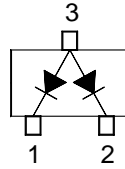
BAW56

Features

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance

Applications

- Ultra high speed switching application



SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	85	V
Continuous Reverse Voltage	V_R	75	V
Forward Current (DC)	I_F	215	mA
Single Diode Loaded		125	
Double Diode Loaded			
Repetitive Peak Forward Current	I_{FRM}	450	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	0.5	A
		1	
		4	

Powe



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Silicon Epitaxial Planar Switching Diode

Typical Characteristics

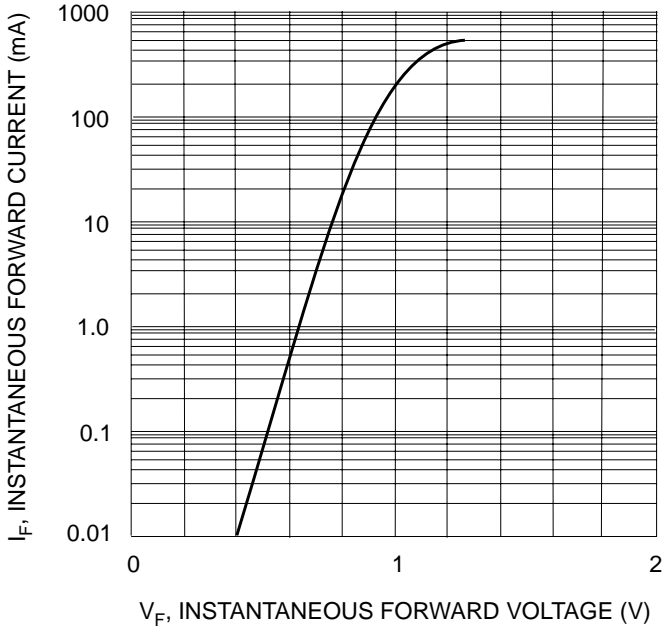


Fig. 1 Forward Characteristics

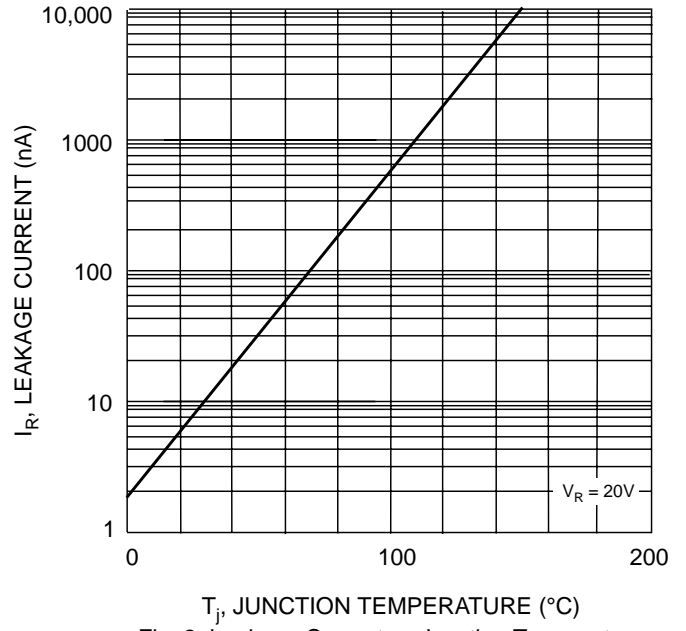


Fig. 2 Leakage Current vs Junction Temperature

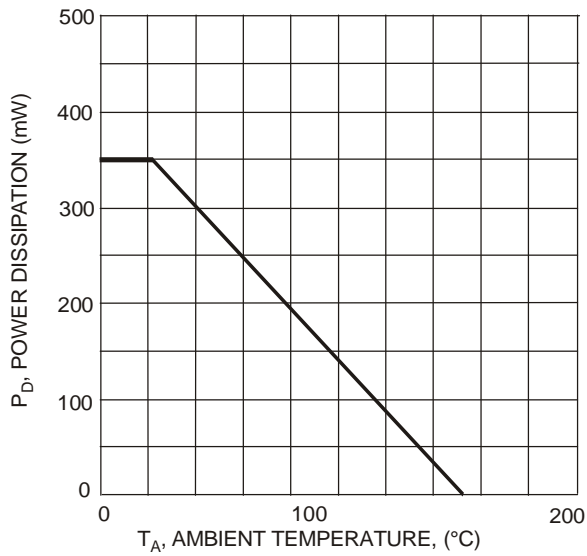
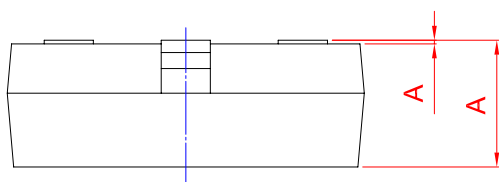
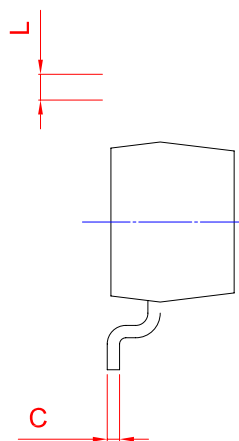
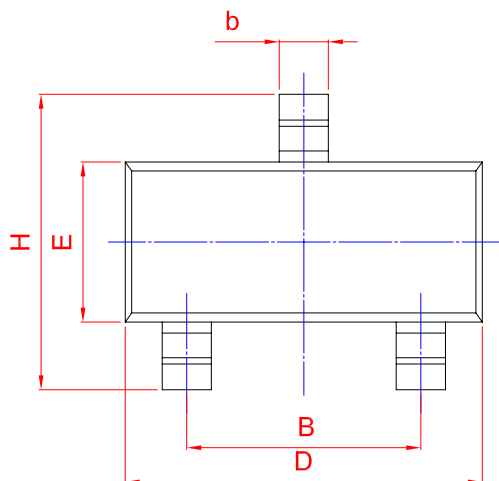
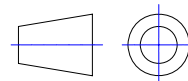


Fig. 3 Power Derating Curve, Total Package



UNIT	A		b_p	C	D	E	H ϵ	A $_1$	
mm	1.40 0.95		0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.5